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# SQD10N30-330H\_GE3

**Vishay Semiconductors** 

MOSFET N Ch 300Vds 30Vgs AEC-Q101 Qualified

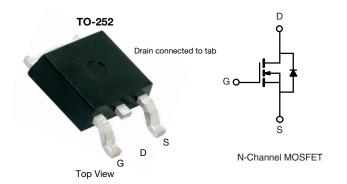
Any questions, please feel free to contact us. info@kaimte.com





## Automotive N-Channel 300 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	300		
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.330		
I <sub>D</sub> (A)	10		
Configuration	Single		



### **FEATURES**

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified <sup>d</sup>
- 100 % R<sub>q</sub> tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





HALOGEN

FREE

ORDERING INFORMATION				
Package	TO-252			
Lead (Pb)-free and Halogen-free	SQD10N30-330H-GE3			

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V <sub>DS</sub>	300	V	
Gate-Source Voltage	$V_{GS}$	± 30		
Continuous Drain Current	T <sub>C</sub> = 25 °C	I-	10	
Continuous Drain Current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	5	
Continuous Source Current (Diode Conduction	I <sub>S</sub>	50	А	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>		16
Single Pulse Avalanche Current <sup>e</sup>	L = 0.05 mH	I <sub>AS</sub>	12.65	
Single Pulse Avalanche Energy <sup>e</sup>	L = 0.05 IIII	E <sub>AS</sub>	4	mJ
Marrian van Darvan Dinain ations h	T <sub>C</sub> = 25 °C	D	107	W
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	$P_{D}$	35	VV
Operating Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	$R_{thJA}$	50	°C/W		
Junction-to-Case (Drain)		R <sub>thJC</sub>	1.4	C/VV	

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.
- e.  $1.5 \text{ k}\Omega$  resistance in series with the gate.

Document Number: 67070

Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static		•						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		300	_	-	.,	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		3.8	4.4	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	: 0 V, V <sub>GS</sub> = ± 30 V	-	-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 300 V	-	-	1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 300 V, T <sub>J</sub> = 125 °C	-		50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 300 V, T <sub>J</sub> = 175 °C	1	-	250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 \text{ V}$	$V_{DS} \ge 5 V$	10	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 14 A	1	0.275	0.330	Ω	
Drain-Source On-State Resistance a	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}$	I <sub>D</sub> = 14 A, T <sub>J</sub> = 125 °C	ı	-	0.733		
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 14 A, T <sub>J</sub> = 175 °C	-	=.	1.000		
Forward Transconductance b	9 <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 14 \text{ A}$		-	26	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>			-	1749	2190		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	112	140	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	44	55		
Total Gate Charge <sup>c</sup>	Qg			-	31	47		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 150 \text{ V}, I_D = 7 \text{ A}$	-	8	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	9.6	-		
Gate Resistance	$R_g$		f = 1 MHz	0.4	0.8	3	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>				10	15		
Rise Time °	t <sub>r</sub>	$V_{DD}$ = 150 V, $R_L$ = 21 $\Omega$ $I_D \cong 7$ A, $V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$		-	18	28	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	20	30		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	8	12		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>	,						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	16	Α	
Forward Voltage	$V_{SD}$	I <sub>E</sub> = 25 A, V <sub>GS</sub> = 0 V		-	0.9	1.5	V	

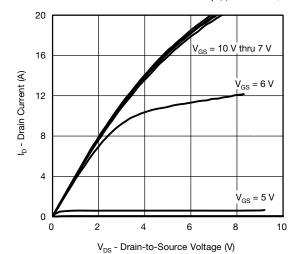
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

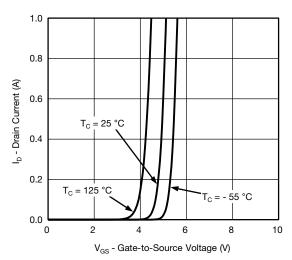
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



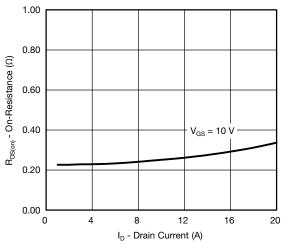
## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



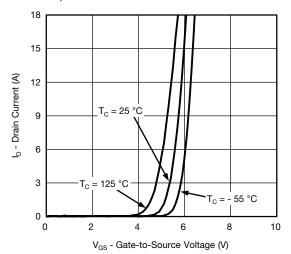
#### **Output Characteristics**



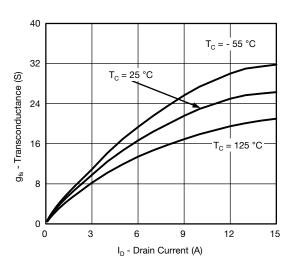
**Transfer Characteristics** 



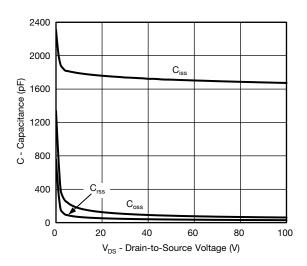
On-Resistance vs. Drain Current



**Transfer Characteristics** 



Transconductance

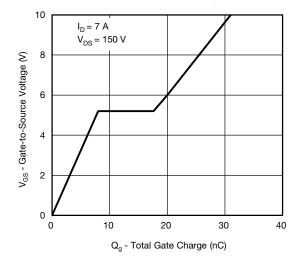


Capacitance

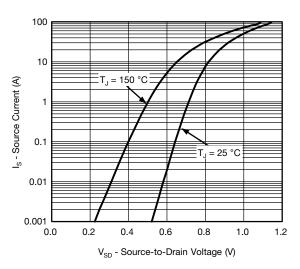
3 Document Number: 67070



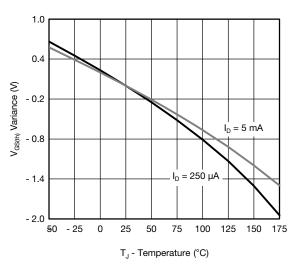
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### **Gate Charge**

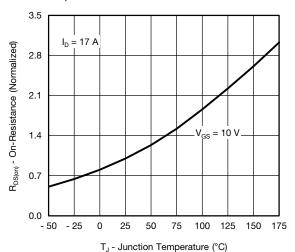


#### Source Drain Diode Forward Voltage

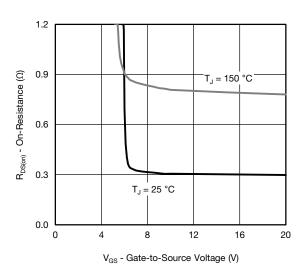


## **Threshold Voltage**

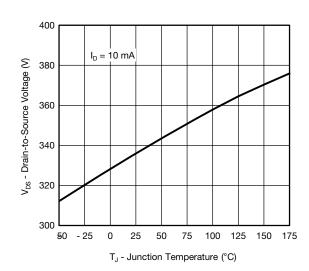
S15-1136-Rev. C, 12-May-15



On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

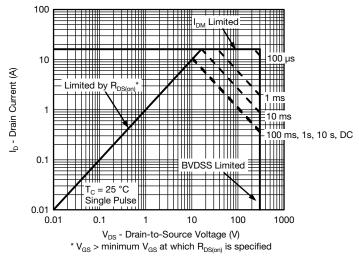


**Drain Source Breakdown vs. Junction Temperature** 

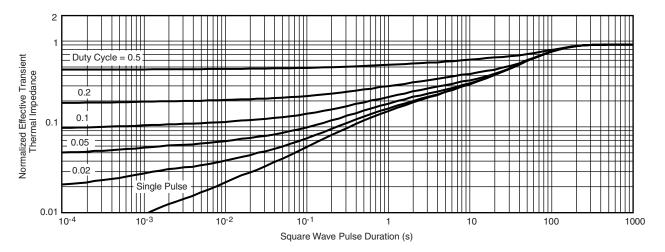
For technical questions, contact: automostechsupport@vishay.com



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



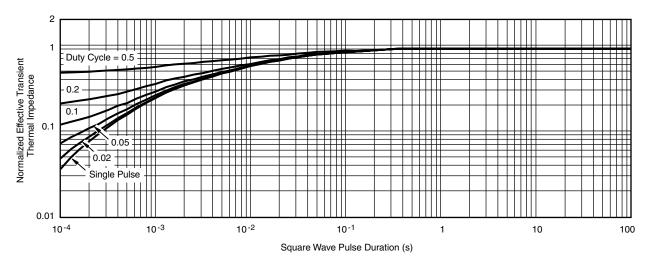
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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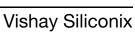
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REVISION HISTORY a					
REVISION	DATE	DESCRIPTION OF CHANGE			
В	26-Feb-2015	UIS changed			
С	04-May-2015	R <sub>g</sub> , C <sub>iss</sub> and t <sub>r</sub> updated			

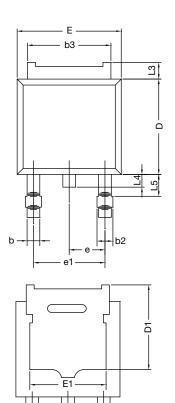
#### Note

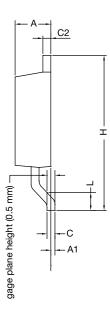
a. As of April 2014





## **TO-252AA Case Outline**





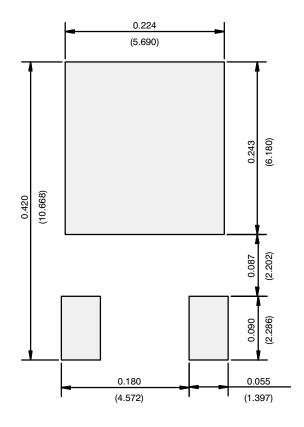
	MILLIN	METERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	=	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	=	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28 BSC		28 BSC 0.090 BSC		
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13					

## DWG: 6019

• Dimension L3 is for reference only.



## **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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